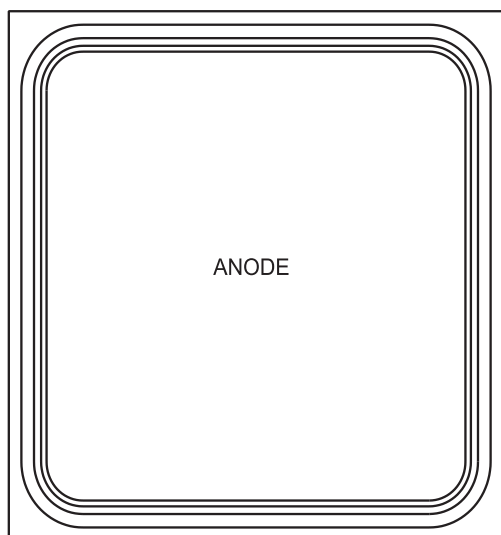


PROCESS DETAILS

Die Size	72.5 x 72.5 MILS
Die Thickness	11.8 MILS
Anode Bonding Pad Area	63.8 x 63.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

2,178

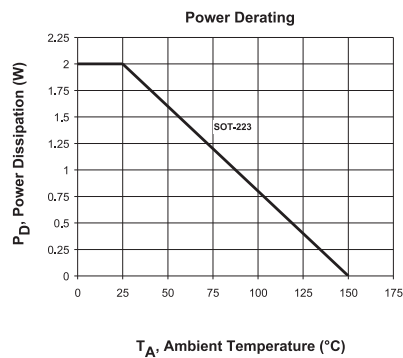
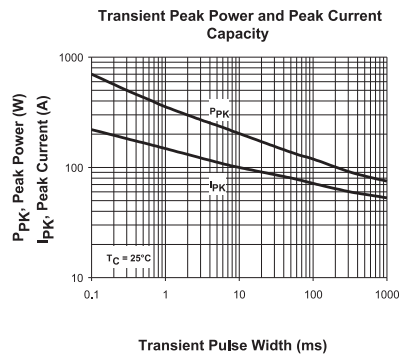
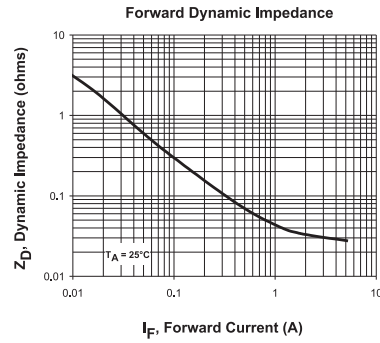
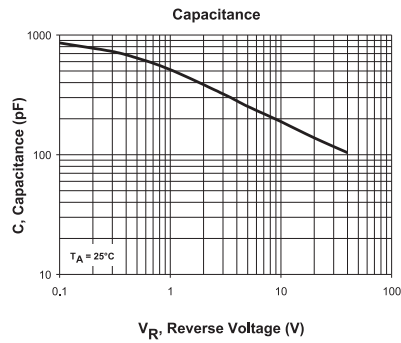
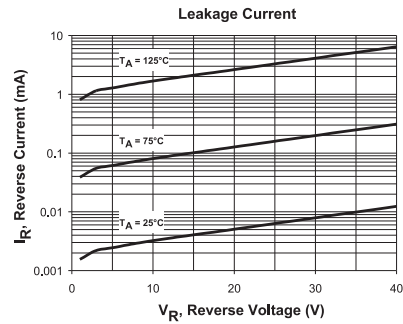
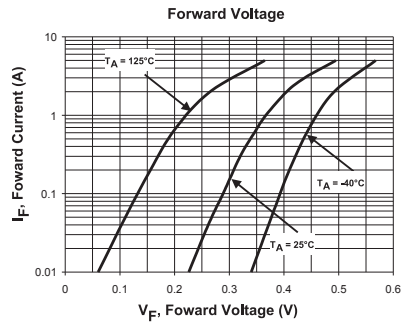
PRINCIPAL DEVICE TYPES

CZSH5-40

CZSH10-40CN (Dual Chip)

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